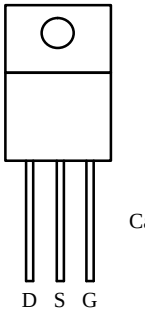
2N7076

N-Channel Enhancement-Mode Transistor

Product Summary

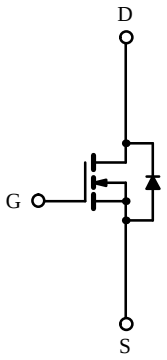
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
200	0.10	28

TO-254AA
Hermetic Package



Case Isolated

Top View



N-Channel MOSFET

Absolute Maximum Ratings (T_C = 25°C Unless Otherwise Noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current (T_J = 150°C)	T_C = 25°C	I_D	28	A
	T_C = 100°C		18	
Pulsed Drain Current		I_{DM}	112	
Maximum Power Dissipation	T_C = 25°C	P_D	150	W
	T_C = 100°C		60	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150	°C
Lead Temperature ($^1/_{16}$" from case for 10 sec.)		T_L	300	

Thermal Resistance Ratings

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient	R_{thJA}		50	°C/W
Maximum Junction-to-Case	R_{thJC}		0.83	
Case-to-Sink	R_{thCS}	0.2		

Subsequent updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #'1453.

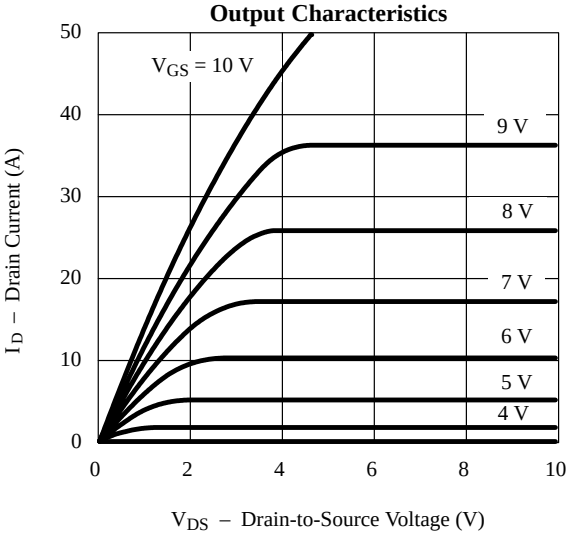
Specifications (T_J = 25°C Unless Otherwise Noted)

Parameter	Symbol	Test Condition	Limit			Unit
			Min	Typ[a]	Max	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 µA	200			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.0		4.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 160 V, V_{GS} = 0 V			25	µA
		V_{DS} = 160 V, V_{GS} = 0 V, T_J = 125°C			250	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	28			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 18 A		0.080	0.10	Ω
		V_{GS} = 10 V, I_D = 18 A, T_J = 125°C		0.15	0.17	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 18 A	9.0	12	27	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		2700		pF
Output Capacitance	C_{oss}			850		
Reverse Transfer Capacitance	C_{rss}			300		
Total Gate Charge[c]	Q_g	V_{DS} = 100 V, V_{GS} = 10 V, I_D = 28 A		63	115	nC
Gate-Source Charge[c]	Q_{gs}			14	21	
Gate-Drain Charge[c]	Q_{gd}			32	60	
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 100 V, R_L = 3.6 Ω I_D ≅ 28 A, V_{GEN} = 10 V, R_G = 2.4 Ω		15	35	ns
Rise Time[c]	t_r			100	150	
Turn-Off Delay Time[c]	$t_{d(off)}$			70	125	
Fall Time[c]	t_f			50	100	
Source-Drain Diode Ratings and Characteristics						
Continuous Current	I_S				28	A
Pulsed Current	I_{SM}				112	
Diode Forward Voltage[b]	V_{SD}	I_F = 28 A, V_{GS} = 0 V	0.6		1.8	V
Reverse Recovery Time	t_{rr}	I_F = 28 A, di/dt = 100 A/µs		175	650	ns
Reverse Recovery Charge	Q_{rr}			0.6		µC

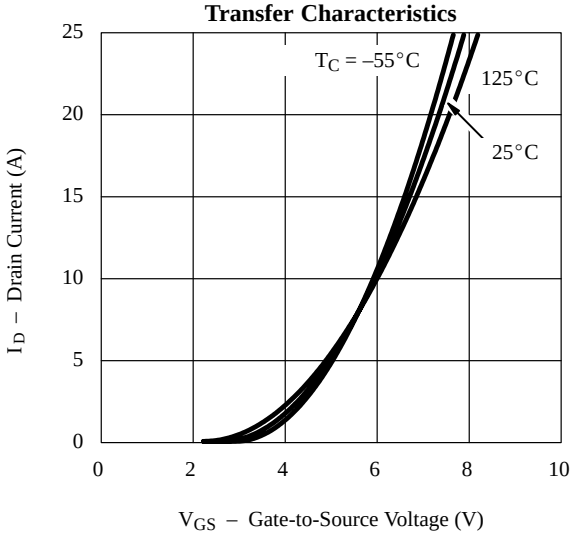
Notes:
a. For design aid only; not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
c. Independent of operating temperature.

Typical Characteristics (25°C Unless Otherwise Noted)

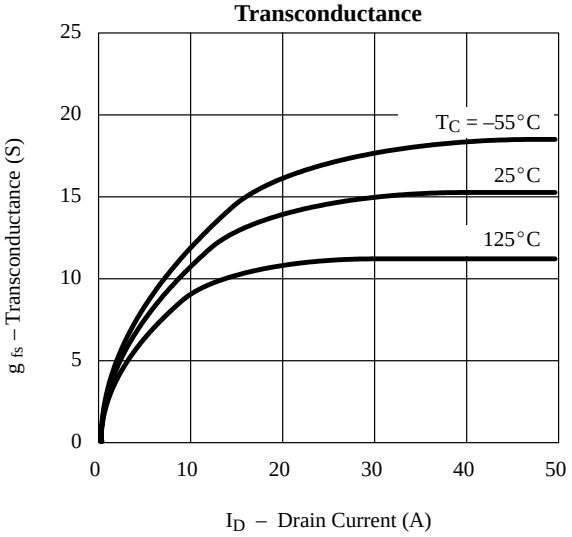
Output Characteristics



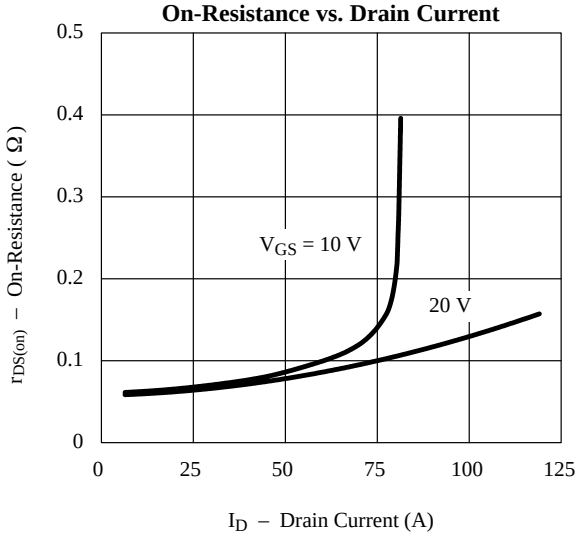
Transfer Characteristics



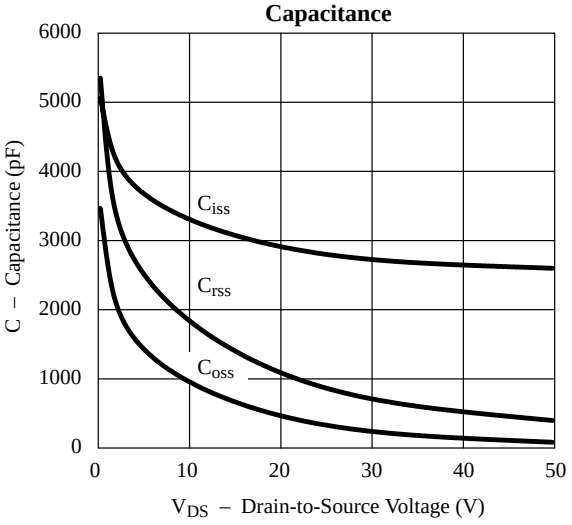
Transconductance



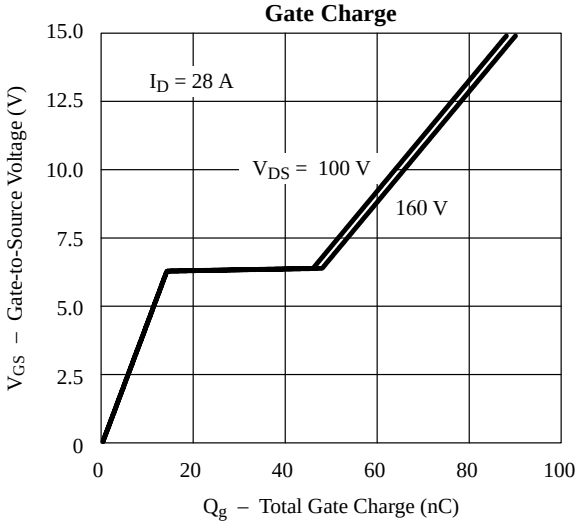
On-Resistance vs. Drain Current



Capacitance

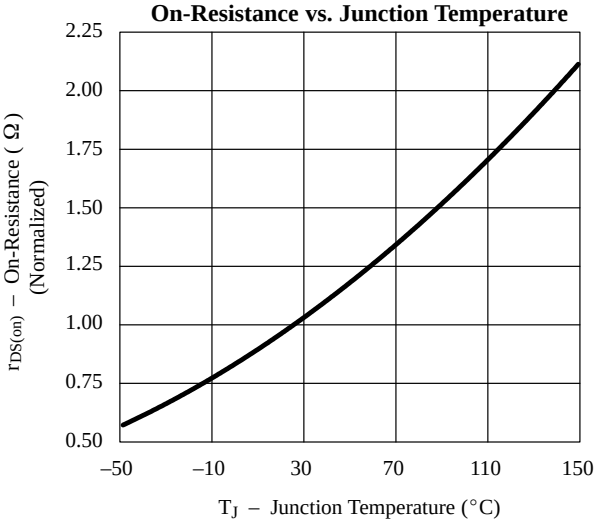


Gate Charge

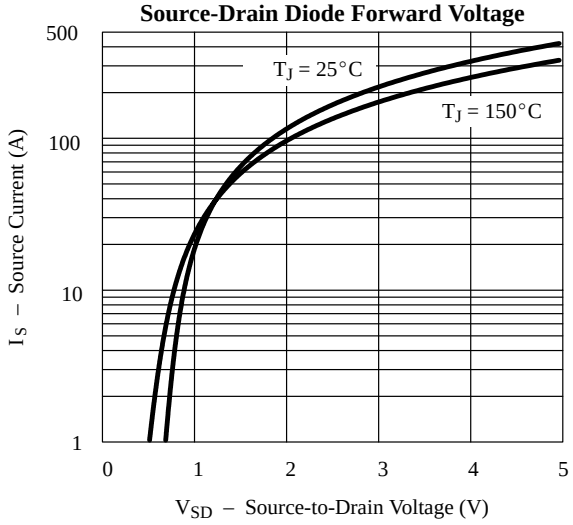


Typical Characteristics (25°C Unless Otherwise Noted)

On-Resistance vs. Junction Temperature

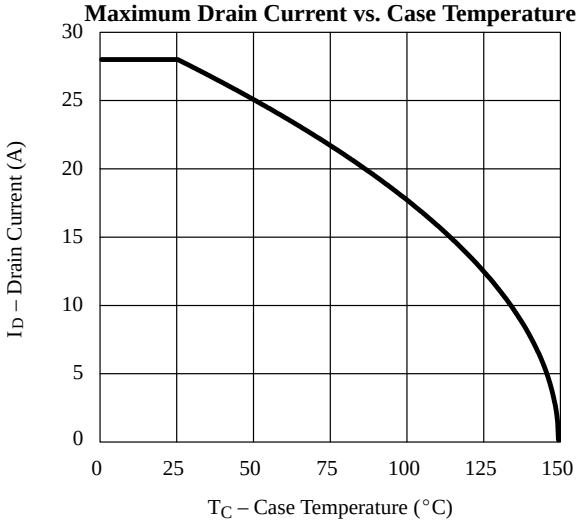


Source-Drain Diode Forward Voltage

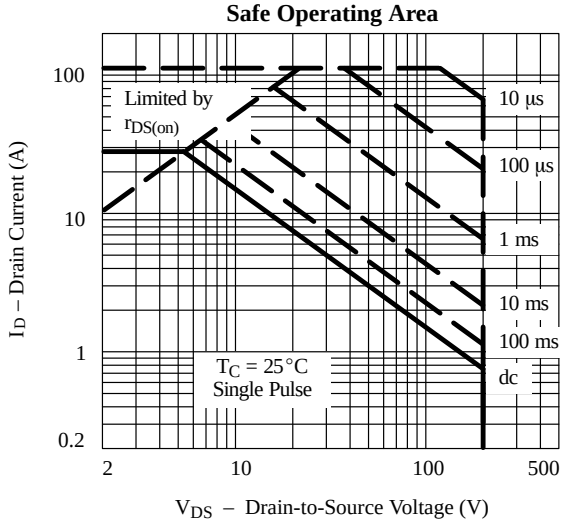


Thermal Ratings

Maximum Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case